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Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China







PIP3213-R

DESCRIPTION

Monolithic single channel high side protected power switch in **TOPFET2** technology assembled in a 5 pin plastic surface mount package.

APPLICATIONS

General controller for driving lamps, motors, solenoids, heaters.

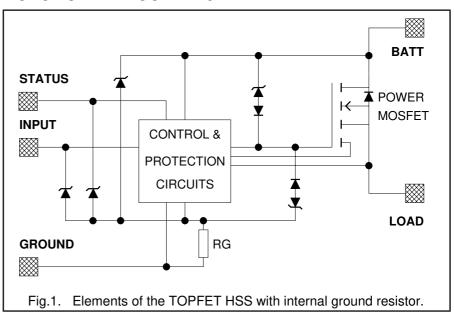
FEATURES

- Vertical power TrenchMOS
- Low on-state resistance
- CMOS logic compatible Very low quiescent current
- Overtemperature protection
- Load current limiting
- Latched overload and short circuit protection
- Overvoltage and undervoltage shutdown with hysteresis
- On-state open circuit load detection
- Diagnostic status indication
- Voltage clamping for turn off of inductive loads
- ESD protection on all pins
- Reverse battery, overvoltage and transient protection

QUICK REFERENCE DATA

SYMBOL	PARAMETER	MIN.	UNIT
I _L	Nominal load current (ISO)	18	Α
SYMBOL	PARAMETER	MAX.	UNIT
V _{BG} L H _{ON}	Continuous off-state supply voltage Continuous load current Continuous junction temperature On-state resistance $T_j = 25^{\circ}C$	50 34 150 20	V A °C mΩ

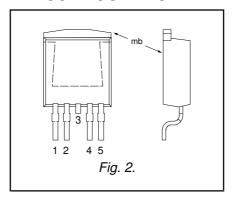
FUNCTIONAL BLOCK DIAGRAM



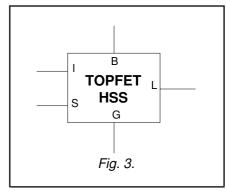
PINNING - SOT426

PIN	DESCRIPTION					
1	Ground					
2	Input					
3	connected to mb)					
4	S tatus					
5	Load					
mb	Battery					

PIN CONFIGURATION



SYMBOL



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LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{BG}	Continuous off-state supply voltage		0	50	V
I _L	Continuous load current	T _{mb} ≤90°C	-	34	Α
P_{D}	Total power dissipation	T _{mb} ≤25°C	-	98	W
T _{stg}	Storage temperature		-55	175	°C
T _j	Continuous junction temperature ¹		-	150	°C
T _{sold}	Mounting base temperature	during soldering	-	260	°C
	Reverse battery voltages ²				
-V _{BG}	Continuous reverse voltage		-	16	V
-V _{BG}	Peak reverse voltage		-	32	V
	Application information				
R _I , R _S	External resistors ³	to limit input, status currents	3.2	-	kΩ
	Input and status				
I _I , I _S	Continuous currents		-5	5	mA
I _I , I _S	Repetitive peak currents	$\delta \leq 0.1$, tp = 300 μs	-50	50	mA
	Inductive load clamping	I _L = 15 A, V _{BG} = 16 V			
E _{BL}	Non-repetitive clamping energy	$T_j = 150$ °C prior to turn-off	-	380	mJ

ESD LIMITING VALUE

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _C	Electrostatic discharge capacitor voltage	Human body model; C = 250 pF; R = 1.5 kΩ	-	2	kV

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
	Thermal resistance⁴					
R _{th j-mb}	Junction to mounting base	-	-	1.0	1.27	K/W

¹ For normal continuous operation. A higher T_j is allowed as an overload condition but at the threshold $T_{j(TO)}$ the over temperature trip operates to protect the switch.

² Reverse battery voltage is allowed only with external resistors to limit the input and status currents to a safe value. The connected load must limit the reverse load current. The internal ground resistor limits the reverse battery ground current. Power is dissipated and the T_j rating must be observed.

³ To limit currents during reverse battery and transient overvoltages (positive or negative).

⁴ Of the output power MOS transistor.

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STATIC CHARACTERISTICS

Limits are at -40 $^{\circ}$ C \leq T_{mb} \leq 150 $^{\circ}$ C and typicals at T_{mb} = 25 $^{\circ}$ C unless otherwise stated.

SYMBOL	PARAMETER	CONDITIO	NS			MIN.	TYP.	MAX.	UNIT
	Clamping voltages								
V_{BG}	Battery to ground	$I_G = 1 \text{ mA}$	$\begin{split} I_G &= 1 \text{ mA} \\ I_L &= I_G = 1 \text{ mA} \\ I_L &= 10 \text{ mA} \\ I_L &= 15 \text{ A}; \ t_p = 300 \mu\text{s} \\ \text{battery to ground} \\ \\ 9 \text{ V} &\leq \text{V}_{BG} \leq 16 \text{ V} \\ \text{V}_{LG} &= 0 \text{ V} \\ \\ \text{V}_{BL} &= \text{V}_{BG} \\ \\ I_L &= 0 \text{ A} \\ \text{V}_{BL} &= 0.5 \text{ V} \\ \\ \hline \text{V}_{BG} & I_L & t_p^7 \\ \hline \\ 9 \text{ to } 35 \text{ V} & 15 \text{ A} & 300 \mu\text{s} \\ \end{split}$			50	55	65	V
V_{BL}	Battery to load	$I_L = I_G = 1 \text{ n}$	nΑ			50	55	65	V
-V _{LG}	Negative load to ground	$I_L = 10 \text{ mA}$				18	23	28	V
-V _{LG}	Negative load voltage ¹	$\begin{split} I_L &= I_G = 1 \text{ mA} \\ I_L &= 10 \text{ mA} \\ I_L &= 15 \text{ A}; \ t_p = 300 \mu\text{s} \\ \end{split}$ battery to ground $\begin{aligned} 9 \text{ V} &\leq \text{V}_{BG} \leq 16 \text{ V} \\ \text{V}_{LG} &= 0 \text{ V} \\ \text{V}_{LG} &= 0 \text{ V} \end{aligned}$ $\begin{aligned} T_{mb} &= 25^{\circ} \\ I_L &= 0 \text{ A} \\ \text{V}_{BL} &= 0.5 \text{ V} \end{aligned}$ $\begin{aligned} T_{mb} &= 85^{\circ} \\ \text{V}_{BG} &\qquad I_L \qquad t_p{}^7 \qquad T_m \\ 9 \text{ to } 35 \text{ V} \qquad 15 \text{ A} \qquad 300 \mu\text{s} \qquad 25 \\ 6 \text{ V} \qquad 15 \text{ A} \qquad 300 \mu\text{s} \qquad 25 \end{aligned}$			20	25	30	V	
	Supply voltage	battery to g	round						
V_{BG}	Operating range ²					5.5	-	35	V
	Currents	9 V ≤ V _{BG} ≤	16 V						
I_{B}	Quiescent current ³	$V_{LG} = 0 V$				-	-	20	μΑ
				T _{mb} =	= 25°C	-	0.1	2	μΑ
I _L	Off-state load current ⁴	$V_{BL} = V_{BG}$				-	-	20	μΑ
				T_{mb} =	= 25°C	-	0.1	1	μΑ
I_{G}	Operating current ⁵	$I_L = 0 A$				-	2	4	mA
IL	Nominal load current ⁶	$V_{BL} = 0.5 V$		T _{mb} =	= 85°C	18	-	-	Α
	Resistances	V_{BG}	I _L	t _p ⁷	T_{mb}				
R_{ON}	On-state resistance	9 to 35 V	15 A	300 μs	25°C	-	15	20	mΩ
					150°C	-	-	37	mΩ
R_{ON}	On-state resistance	6 V	15 A	300 μs	25°C	-	18	25	mΩ
					150°C	-	-	45	mΩ
R_{G}	Internal ground resistance	I _G = 10 mA	•	•	•	95	150	190	Ω

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¹ For a high side switch, the load pin voltage goes negative with respect to ground during the turn-off of an inductive load.

 $^{{\}bf 2}$ On-state resistance is increased if the supply voltage is less than 9 V. Refer to figure 8.

³ This is the continuous current drawn from the supply when the input is low and includes leakage current to the load.

⁴ The measured current is in the load pin only.

⁵ This is the continuous current drawn from the supply with no load connected, but with the input high.

 $^{{\}bf 6}$ Defined as in ISO 10483-1. For comparison purposes only.

⁷ The supply and input voltage for the R_{ON} tests are continuous. The specified pulse duration t₀ refers only to the applied load current.

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INPUT CHARACTERISTICS

9 V \leq V_{BG} \leq 16 V. Limits are at -40°C \leq T_{mb} \leq 150°C and typicals at T_{mb} = 25 °C unless otherwise stated.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I ₁	Input current	$V_{IG} = 5 V$	20	90	160	μΑ
V_{IG}	Input clamping voltage	Ι _ι = 200 μΑ	5.5	7	8.5	V
$V_{IG(ON)}$	Input turn-on threshold voltage		-	2.4	3	V
$V_{\text{IG}(\text{OFF})}$	Input turn-off threshold voltage		1.5	2.1	-	V
ΔV_{IG}	Input turn-on hysteresis		-	0.3	-	V
I _{I(ON)}	Input turn-on current	$V_{IG} = 3 V$	-	-	100	μΑ
$I_{I(OFF)}$	Input turn-off current	V _{IG} = 1.5 V	10	-	-	μΑ

STATUS CHARACTERISTICS

The status output is an open drain transistor, and requires an external pull-up circuit to indicate a logic high. Limits are at -40 $^{\circ}$ C \leq T_{mb} \leq 150 $^{\circ}$ C and typicals at T_{mb} = 25 $^{\circ}$ C unless otherwise stated. Refer to TRUTH TABLE.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{SG}	Status clamping voltage	I _S = 100 μA	5.5	7	8.5	V
V_{SG}	Status low voltage	$I_{S} = 100 \mu\text{A}$	-	-	1	V
		$T_{mb} = 25^{\circ}C$	-	0.7	0.8	V
Is	Status leakage current	$V_{SG} = 5 \text{ V}$	-	-	15	μА
		$T_{mb} = 25^{\circ}C$	-	0.1	1	μΑ
Is	Status saturation current ¹	$V_{SG} = 5 \text{ V}$	2	7	12	mA
	Application information					
R _s	External pull-up resistor		-	47	-	kΩ

OPEN CIRCUIT DETECTION CHARACTERISTICS

An open circuit load can be detected in the on-state. Refer to TRUTH TABLE. Limits are at -40 $^{\circ}$ C \leq T_{mb} \leq 150 $^{\circ}$ C and typical is at T_{mb} = 25 $^{\circ}$ C.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
	Open circuit detection	$9 \text{ V} \leq \text{V}_{\text{BG}} \leq 35 \text{ V}$				
I _{L(TO)}	Low current detect threshold		0.45	1.5	3	Α
$\Delta I_{L(TO)}$	Hysteresis		-	0.3	-	Α

¹ In a fault condition with the pull-up resistor short circuited while the status transistor is conducting. This condition should be avoided in order to prevent possible interference with normal operation of the device.

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UNDERVOLTAGE & OVERVOLTAGE CHARACTERISTICS

Limits are at -40 °C \leq T_{mb} \leq 150 °C and typicals at T_{mb} = 25 °C. Refer to TRUTH TABLE.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
	Undervoltage					
$V_{BG(UV)}$	Low supply threshold voltage ¹		2	4.2	5.5	٧
$\Delta V_{BG(UV)}$	Hysteresis		-	0.5	-	٧
	Overvoltage					
$\begin{vmatrix} V_{BG(OV)} \\ \Delta V_{BG(OV)} \end{vmatrix}$	High supply threshold voltage ² Hysteresis		40 -	45 1	50 -	V V

TRUTH TABLE

	AE	BNORMA DE	AL CON TECTE		S	LOAD		
INPUT	SUP	PLY		LOAD		OUTPUT	STATUS	DESCRIPTION
	UV	ov	LC	SC	ОТ			
L	Х	Х	X X X		OFF	Н	off	
Н	0	0	0	0	0	ON	Н	on & normal
Н	0	0	1	0	0	ON	L	on & low current detect
Н	1	0	Х	Χ	Х	OFF	Н	supply undervoltage lockout
Н	0	1	Х	0	0	OFF	Н	supply overvoltage shutdown
Н	0	0	0	1	Х	OFF	L	SC tripped
Н	0	0	0	0	1	OFF	L	OT shutdown ³

KEY TO ABBREVIATIONS

logic low

Н loğic high

don't care

condition not present

condition present

UV undervoltage

OV overvoltage
LC low current or open circuit load
SC short circuit

OT overtemperature

 $^{{\}bf 1}$ Undervoltage sensor causes the device to switch off and reset.

² Overvoltage sensor causes the device to switch off to protect its load.

³ The status will continue to indicate OT (even if the input goes low) until the device cools below the reset threshold. Refer to OVERLOAD PROTECTION CHARACTERISTICS.

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OVERLOAD PROTECTION CHARACTERISTICS

 $5.5~V \le V_{BG} \le 35~V$, limits are at -40°C $\le T_{mb} \le 150$ °C and typicals at $T_{mb} = 25~$ °C unless otherwise stated. Refer to TRUTH TABLE.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$I_{L(lim)}$	Overload protection Load current limiting	$V_{BL} = V_{BG}$ $V_{BG} \ge 9 V$	42	65	88	А
$V_{BL(TO)}$ t_{dsc}	Short circuit load protection Battery load threshold voltage ¹ Response time ²	$V_{BG} = 16 \text{ V}$ $V_{BG} = 35 \text{ V}$ $V_{BL} > V_{BL(TO)}$	8 15 -	10 20 180	12 25 250	V V μs
$T_{j(TO)}$ $\Delta T_{j(TO)}$	Overtemperature protection Threshold junction temperature ³ Hysteresis		150	170 10	190	°C

SWITCHING CHARACTERISTICS

 T_{mb} = 25 °C, V_{BG} = 13 V, for resistive load R_L = 13 Ω .

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
	During turn-on	from input going high				
t _{d on}	Delay time	to 10% V _L	-	40	60	μs
dV/dt _{on}	Rate of rise of load voltage	30% to 70% V _L	-	0.5	1	V/μs
t on	Total switching time	to 90% V _L	-	160	225	μs
	During turn-off	from input going low				
t _{d off}	Delay time	to 90% V _L	-	50	70	μs
dV/dt _{off}	Rate of fall of load voltage	70% to 30% V _L	-	0.5	1	V/μs
t off	Total switching time	to 10% V _L	-	80	115	μs

CAPACITANCES

 $T_{mb} = 25$ °C; f = 1 MHz; $V_{IG} = 0$ V. designed in parameters.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
C _{ig}	Input capacitance	V _{BG} = 13 V	-	15	20	pF
C _{bl}	Output capacitance	V _{BL} = 13 V	-	425	600	pF
C_{sg}	Status capacitance	$V_{SG} = 5 V$	-	11	15	рF

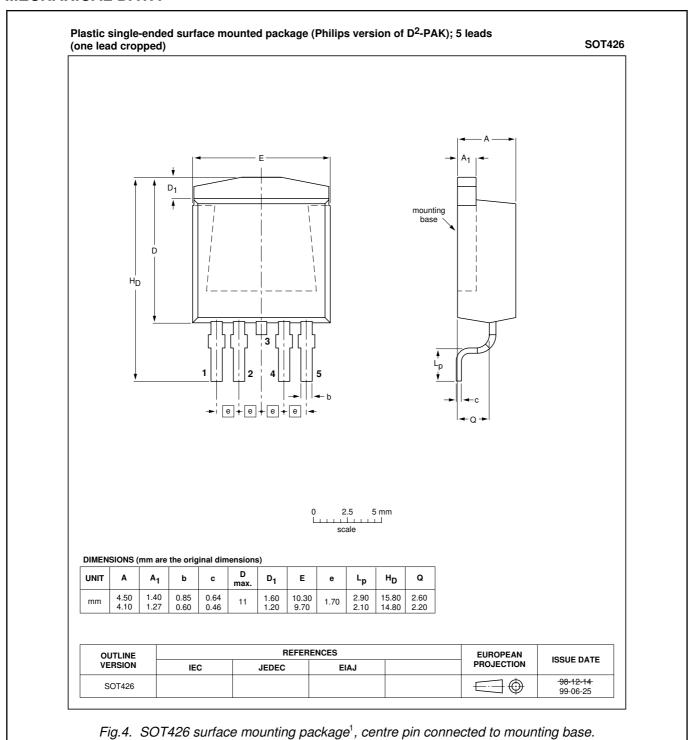
¹ The battery to load threshold voltage for short circuit protection is proportional to the battery supply voltage. After short circuit protection has operated, the input voltage must be toggled low for the switch to resume normal operation.

² Measured from when the input goes high.

³ After cooling below the reset temperature the switch will resume normal operation.

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MECHANICAL DATA



¹ Epoxy meets UL94 V0 at 1/8". Net mass: 1.5 g. For soldering guidelines and SMD footprint design, please refer to Data Handbook SC18.

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DEFINITIONS

DATA SHEET STATUS				
DATA SHEET STATUS ¹	PRODUCT STATUS ²	DEFINITIONS		
Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice		
Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in ordere to improve the design and supply the best possible product		
Product data	Production	This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Changes will be communicated according to the Customer Product/Process Change Notification (CPCN) procedure SNW-SQ-650A		

Limiting values

Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information

Where application information is given, it is advisory and does not form part of the specification.

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² The product status of the device(s) described in this datasheet may have changed since this datasheet was published. The latest information is available on the Internet at URL http://www.semiconductors.philips.com.